

Claim Amendments

1. (currently amended) A production process for compound semiconductor particles, which comprises:

- a) the step of heating and/or polish-pulverizing i) a first mixture including a metal carboxylate, an alcohol, and particles or ii) a second mixture including a metal-alkoxy-group-containing compound, a carboxyl-group-containing compound, and particles,
- b) thereby covering the particles with a metal oxide,
- c) wherein the particles include a compound semiconductor.

2. (original) A production process for compound semiconductor particles according to claim 1, wherein the particles including the compound semiconductor are particles as obtained by a process including the step of polish-pulverizing coarse particles of the compound semiconductor to thereby fine the particles.

3. (original) A production process for compound semiconductor particles, which comprises the steps of: polish-pulverizing coarse particles of a compound semiconductor to thereby obtain particles having particle diameters of smaller than 1 μm ; and then covering the resultant particles with a metal oxide.

4. (original) Compound semiconductor particles, which comprise body particles and a metal oxide, wherein the body particles have particle diameters of smaller than 1 μm and are covered with the metal oxide and include a compound semiconductor including an essential element combination of at least one element X selected from the group consisting of

C, Si, Ge, Sn, Pb, N, P, As, S, Sb, Se, and Te and at least one metal element M that is not identical with the element X, and wherein the metal oxide is a metal oxide to which an acyloxyl group is bonded.

5. (original) Compound semiconductor particles according to claim 4, wherein the body particles are particles as obtained by a process including the step of polish-pulverizing coarse particles of the compound semiconductor including the essential element combination of at least one element X selected from the group consisting of C, Si, Ge, Sn, Pb, N, P, As, Sb, S, Se, and Te and at least one metal element M that is not identical with the element X.